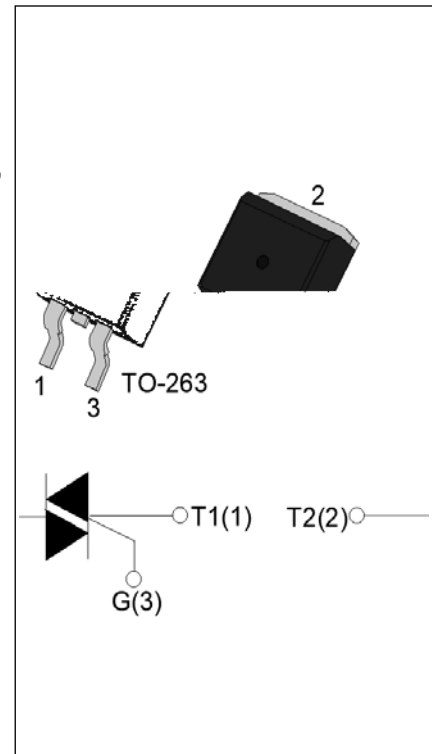




The T2035H-6E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T2035H-6E provides a very high switching capability up to junction temperatures of 150°C. Package TO-263 is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	20	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III}$	35/35/35	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	600	V
RMS on-state current ($T_c \leq 121^\circ\text{C}$)	$I_{T(RMS)}$	20	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	200	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		220	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	200	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current ($t_p=20\mu\text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W

Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)	V_{pp}	4	kV
------------------------------------------------------------------------------------	----------	---	----

(T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V } R_L=33$	I - II - III	MAX.	35	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150^\circ\text{C}$ $R_L=3.3\text{K}$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	50	mA
		II		80	
I_H	$I_T=500\text{mA}$		MAX.	35	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=150^\circ\text{C}$		MIN.	1800	V/ μs
(dI/dt) _c	(dV/dt) _c =20V/ μs , $T_j=150^\circ\text{C}$		MIN.	20	A/ms
t_{on}	$I_G=40\text{mA } I_A=200\text{mA } I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	8	μs
t_{off}				70	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=28\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^\circ\text{C}$	0.71	V
R_D	Dynamic resistance	$T_j=150^\circ\text{C}$	22	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=150^\circ\text{C}$	2.5	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.1	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=2\text{cm}^2$)	45	$^\circ\text{C/W}$

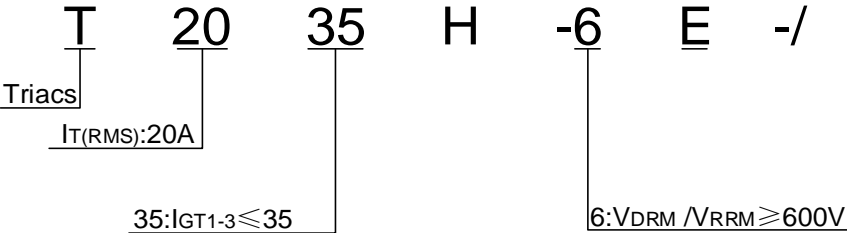


FIG.1 Maximum power dissipation versus RMS on-state current

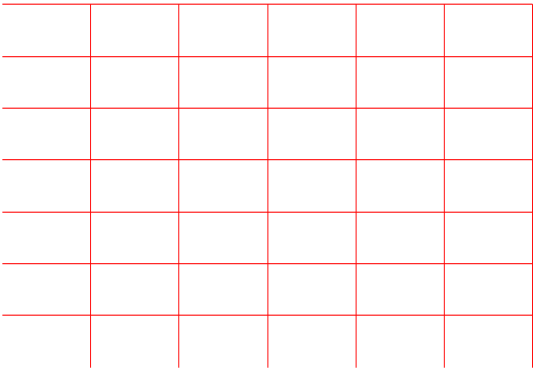


FIG.2: RMS on-state current versus case temperature

FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

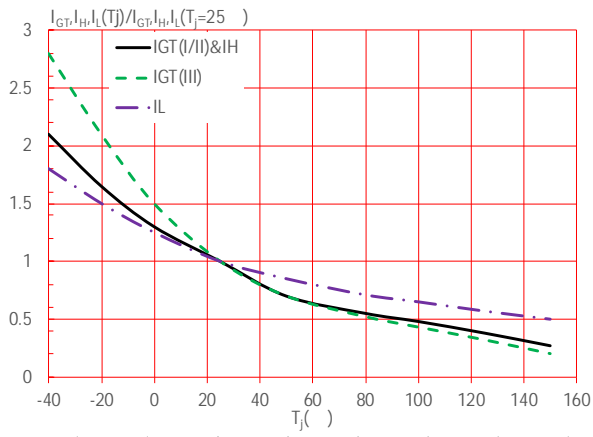
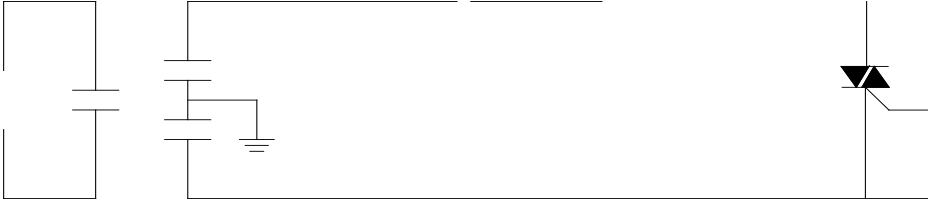


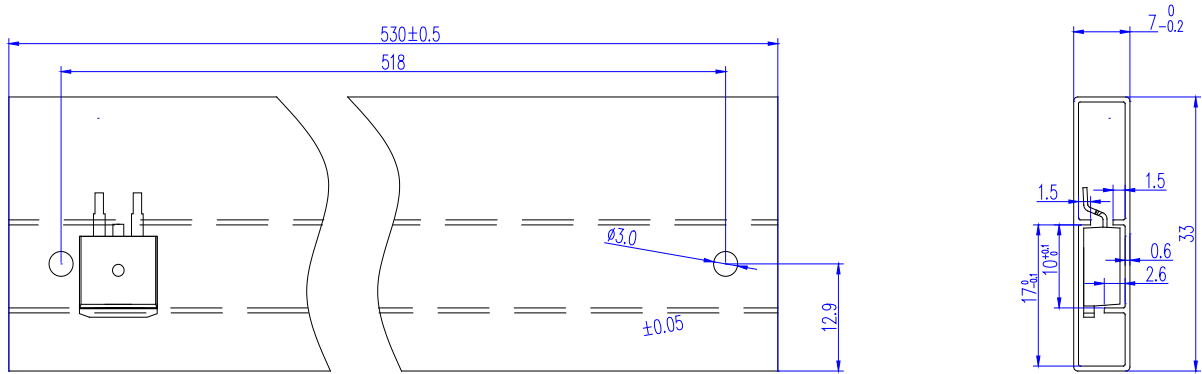
FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



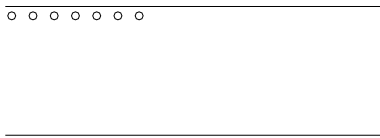
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
T2035H-6E	600	35	TO-263	50	Tube
T2035H-6E-TR				800	Tape & Reel

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-263	TUBE	50	1,000	5,000



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	23.70	24.00	24.30	0.933	0.945	0.957
E	1.65	1.75	1.85	0.065	0.069	0.073
F	11.40	11.50	11.60	0.449	0.453	0.457
D0	-	1.50	1.60	-	0.059	0.063
D1	-	1.50	1.60	-	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	15.90	16.00	16.10	0.626	0.630	0.634
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	10.80	10.90	11.00	0.425	0.429	0.433
B0	16.20	16.30	16.40	0.638	0.642	0.646
K0	4.80	4.90	5.00	0.189	0.193	0.197
t	0.35	0.40	0.45	0.014	0.016	0.018

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